



MLX92211LSE

*Hall Effect Latch – 2nd Generation
High Sensitivity*

Features and Benefits

- Wide operating voltage range : from 2.7V to 24V
- Very high magnetic sensitivity : +/-3mT typical
- Chopper-stabilized amplifier stage
- Built-in negative temperature coefficient : -1100ppm/degC
- Reverse Supply Voltage Protection
- Output Current Limit with Auto-Shutoff
- Under-Voltage Lockout Protection
- Thermal Protection
- High ESD rating / Excellent EMC performance
- Thin SOT23 3L Green Compliant package

Application Examples

- Automotive, Consumer and Industrial
- Solid-state switch
- 3-phase BLDC motor commutation
- Wiper motor
- Window lifter
- Sunroof/Tailgate opener
- Seat motor adjuster
- Electrical power steering

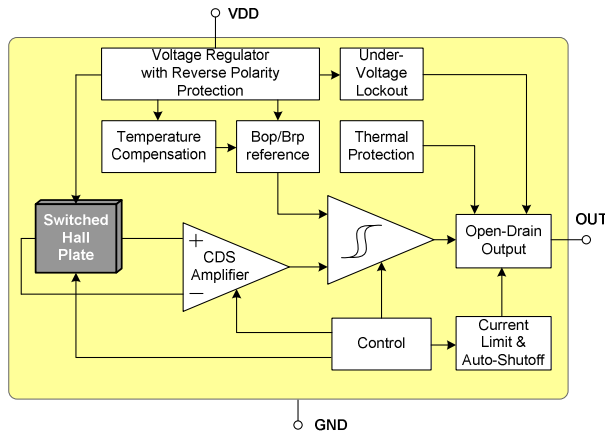
Ordering Code

Product Code	Temperature Code	Package Code	Option Code	Packing Form Code
MLX92211	L	SE	AAA-000	RE

Legend:

Temperature Code:	L for Temperature Range -40°C to 150°C
Package Code:	SE for TSOT 3 UP
Option Code:	xxx-000: Standard version
Packing Form:	RE for Reel
Order example:	MLX92211LSE-AAA-000-RE

1 Functional Diagram



behaviour of magnets becoming weaker with rise in temperature.

The included voltage regulator operates from 2.7 to 24V, hence covering a wide range of applications. With the built-in reverse voltage protection, a serial resistor or diode on the supply line is not required so that even remote sensors can be specified for low voltage operation down to 2.7V while being reverse voltage tolerant.

In the event of a drop below the minimum supply voltage during operation, the under-voltage lock-out protection will automatically freeze the device, preventing the electrical perturbation to affect the magnetic measurement circuitry. The output state is therefore only updated based on a proper and accurate magnetic measurement result.

2 General Description

The Melexis MLX92211 is the second generation Hall-effect latch designed in mixed signal CMOS technology. The device integrates a voltage regulator, Hall sensor with advanced offset cancellation system and an open-drain output driver, all in a single package.

Based on a brand new platform, the magnetic core is using an improved offset cancellation system allowing faster and more accurate processing while being temperature insensitive and stress independent. In addition is implemented a negative temperature coefficient of -1100ppm/degC to compensate the natural

The open drain output is fully protected against short-circuit with a built-in current limit. An additional automatic output shut-off is activated in case of a prolonged short-circuit condition. A self-check is then periodically performed to switch back to normal operation if the short-circuit condition is released. The on-chip thermal protection also switches off the output if the junction temperature increases above an abnormally high threshold. It will automatically recover once the temperature decreases below a safe value.

With latching magnetic characteristics, the output is turned low or high respectively with a sufficiently strong South or North pole facing the package top side. When removing the magnetic field, the device keeps its previous state.



MLX92211LSE

Hall Effect Latch – 2nd Generation High Sensitivity

Table of Contents

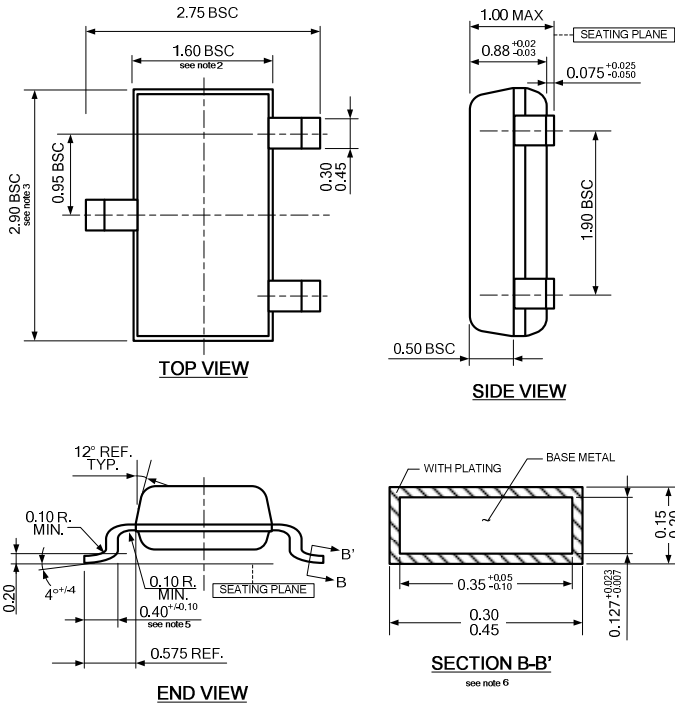
1 Functional Diagram	2
2 General Description	2
3 Glossary of Terms	5
4 Absolute Maximum Ratings	5
5 General Electrical Specifications	6
6 Magnetic Specifications	7
7 Output Behaviour versus Magnetic Pole	7
Performance Graphs	8
7.1 Magnetic parameters vs. T_A	8
7.2 Magnetic parameters vs. V_{DD}	8
7.3 V_{DSon} vs. T_A	8
7.4 V_{DSon} vs. V_{DD}	8
7.5 I_{DD} vs. T_A	8
7.6 I_{DD} vs. V_{DD}	8
7.7 I_{LEAK} vs. T_A	9
7.8 I_{LEAK} vs. V_{DD}	9
7.9 Power Derating vs. T_A	9
8 Application Information	10
8.1 Typical Three-Wire Application Circuit.....	10
8.2 Automotive and Harsh, Noisy Environments Three-Wire Circuit.....	10
9 Standard information regarding manufacturability of Melexis products with different soldering processes	11
10 ESD Precautions	11
11 SE Package (TSOT-23)	12



MLX92211LSE

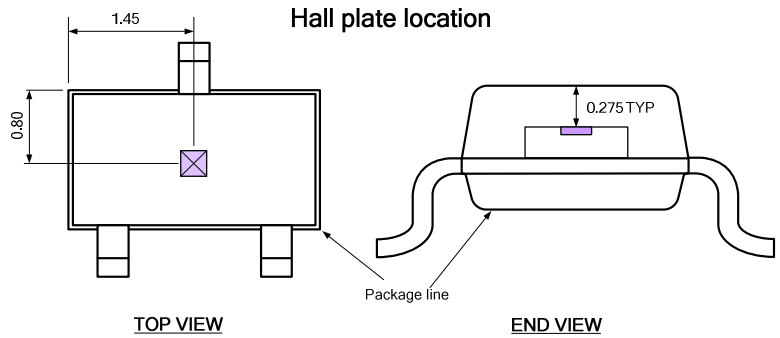
Hall Effect Latch – 2nd Generation High Sensitivity

11.1 Package Outline Drawing & Hall Plate Position



- Notes:**
1. All dimensions are in millimeters
 2. Outermost plastic extreme width does not include mold flash or protrusions. Mold flash and protrusions shall not exceed 0.15mm per side.
 3. Outermost plastic extreme length does not include mold flash or protrusions. Mold flash and protrusions shall not exceed 0.25mm per side.
 4. The lead width dimension does not include dambar protrusion. Allowable dambar protrusion shall be 0.07mm total in excess of the lead width dimension at maximum material condition.
 5. Dimension is the length of terminal for soldering to a substrate.
 6. Dimension on SECTION B-B' applies to the flat section of the lead between 0.08mm and 0.15mm from the lead tip.
 7. Formed lead shall be planar with respect to one another with 0.076mm at seating plane.

Marking:
 Top side :
 Bottom side:



- Notes:**
1. All dimensions are in millimeters

..... 12
12 Disclaimer **13**



MLX92211LSE

Hall Effect Latch – 2nd Generation High Sensitivity

3 Glossary of Terms

MilliTesla (mT), Gauss	Units of magnetic flux density: 1mT = 10 Gauss
RoHS	Restriction of Hazardous Substances
TSOT	Thin Small Outline Transistor (TSOT package) – also referred with the Melexis package code “SE”
ESD	Electro-Static Discharge

4 Absolute Maximum Ratings

Parameter	Symbol	Value	Units
Supply Voltage ^(1, 2)	V _{DD}	+27	V
Supply Current ^(1, 2, 3)	I _{DD}	+20	mA
Supply Current ^(1, 4, 3)	I _{DD}	+50	mA
Reverse Supply Voltage ^(1, 2)	V _{DDREV}	-27	V
Reverse Supply Current ^(1, 5, 2)	I _{DDREV}	-20	mA
Reverse Supply Current ^(1, 4, 5)	I _{DDREV}	-50	mA
Output Voltage ^(1, 2)	V _{OUT}	+27	V
Output Current ^(1, 5, 2)	I _{OUT}	+20	mA
Output Current ^(1, 4, 6)	I _{OUT}	+75	mA
Reverse Output Voltage ⁽¹⁾	V _{OUTREV}	-0.5	V
Reverse Output Current ^(1, 2)	I _{OUTREV}	-50	mA
Operating Temperature Range	T _A	-40 to +150	°C
Storage Temperature Range	T _S	-55 to +165	°C
Maximum Junction Temperature ⁽⁷⁾	T _J	+165	°C
ESD Sensitivity – HBM ⁽⁸⁾	-	4000	V
ESD Sensitivity – MM ⁽⁹⁾	-	500	V
ESD Sensitivity – CDM ⁽¹⁰⁾	-	1000	V
Magnetic Flux Density	B	Unlimited	mT

Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

¹ The maximum junction temperature should not be exceeded

² For maximum 1 hour

³ Including current through protection device

⁴ For maximum 1s

⁵ Through protection device

⁶ For V_{out} ≤ 27V.

⁷ For 1000 hours.

⁸ Human Model according AEC-Q100-002 standard

⁹ Machine Model according AEC-Q100-003 standard

¹⁰ Charged Device Model according AEC-Q100-011 standard



MLX92211LSE

Hall Effect Latch – 2nd Generation
High Sensitivity

5 General Electrical Specifications

DC Operating Parameters $T_A = -40^{\circ}\text{C}$ to 150°C , $V_{DD} = 2.7\text{V}$ to 24V (unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ ⁽¹⁾	Max	Units
Supply Voltage	V_{DD}	Operating	2.7	-	24	V
Supply Current	I_{DD}		1.5	3.0	4.5	mA
Reverse Supply Current	I_{DDREV}	$V_{DD} = -18\text{V}$			1	mA
Output Leakage Current	I_{OFF}	$V_{OUT} = 12\text{V}$, $V_{DD} = 12\text{V}$, $B < B_{rp}$		0.1	10	μA
Output Saturation Voltage	V_{OL}	$B > B_{OP}$, $V_{DD} = 3.8$ to 18V , $I_{OUT} = 20\text{mA}$		0.2	0.5	V
Output Rise Time ⁽²⁾ (R_{PU} dependent)	t_R	$V_{DD} = 12\text{V}$, $V_{PU}^{(3)} = 5\text{V}$, $R_{PU} = 1\text{k}\Omega$ $C_{LOAD} = 50\text{pF}$ to GND	0.1	0.3	1	μs
Output Fall Time ⁽²⁾ (On-chip controlled)	t_F	$V_{DD} = 12\text{V}$, $V_{PU} = 5\text{V}$, $R_{PU} = 1\text{k}\Omega$ $C_{LOAD} = 50\text{pF}$ to GND	0.1	0.3	1	μs
Output Current Limit	I_{CL}	$B > B_{OP}$, $V_{DD} = 3.8$ to 18V , $V_{OUT} = 12\text{V}$	22	40	70	mA
Output ON Time under Current Limit conditions ⁽⁴⁾	t_{CLON}	$B > B_{OP}$, $V_{PU} = 12\text{V}$, $R_{PU} = 100\Omega$	150	240		μs
Output OFF Time under Current Limit conditions ⁽⁴⁾	t_{CLOFF}	$B > B_{OP}$, $V_{PU} = 12\text{V}$, $R_{PU} = 100\Omega$		3.5		ms
Chopping Frequency	f_{CHOP}			340		kHz
Output Refresh Period ⁽²⁾	t_{PER}			6		μs
Delay time ^(2,5)	t_D	Average over 1000 successive switching events @10kHz, square wave with $B \geq 30\text{mT}$, $t_{RISE} = t_{FALL} \leq 20\mu\text{s}$		6		μs
Output Jitter (p-p) ^(2,6)	t_{JITTER}	Over 1000 successive switching events @1kHz, square wave with $B \geq 30\text{mT}$, $t_{RISE} = t_{FALL} \leq 100\mu\text{s}$		± 3		μs
Maximum Switching Frequency ^(2,7)	f_{SW}	$B \geq 30\text{mT}$ and square wave magnetic field	30	50		kHz
Power-On Time ^(8,9)	t_{ON}	$V_{DD} = 5\text{V}$, $dV_{DD}/dt > 2\text{V}/\mu\text{s}$		16	35	μs
Under-voltage Lockout Threshold	V_{UVL}		2.2	2.4	2.7	V
Under-voltage Lockout Reaction time ⁽²⁾	t_{UVL}			1		μs
Thermal Protection Threshold	T_{PROT}	Junction temperature		185 ⁽⁹⁾		$^{\circ}\text{C}$
Thermal Protection Release	T_{REL}	Junction temperature		170 ⁽⁹⁾		$^{\circ}\text{C}$
SE Package Thermal Resistance	R_{TH}	Single layer (1S) Jedec board		300		$^{\circ}\text{C}/\text{W}$

Table 1: Electrical specifications

¹ Typical values are defined at $T_A = +25^{\circ}\text{C}$ and $V_{DD} = 12\text{V}$, unless otherwise specified

² Guaranteed by design and verified by characterization, not production tested

³ R_{PU} and V_{PU} are respectively the external pull-up resistor and pull-up power supply

⁴ If the Output is in Current Limitation longer than t_{CLON} the Output is switched off in high-impedance state. The Output returns back in active state at next reaching of B_{OP} or after t_{CLOFF} time interval

⁵ The Delay Time is the time from magnetic threshold reached to the start of the output switching

⁶ Output jitter is the unpredictable deviation of the Delay time

⁷ Maximum switching frequency corresponds to the maximum frequency of the applied magnetic field which is detected without loss of pulses

⁸ The Power-On Time represents the time from reaching $V_{DD} = V_{POR}$ to the first refresh of the output (first valid output state)

⁹ Power-On Slew Rate should not be critical for the proper device start-up



MLX92211LSE

Hall Effect Latch – 2nd Generation
High Sensitivity

6 Magnetic Specifications

DC Operating Parameters $V_{DD} = 3.8V$ to $24V$ and $T_A = -40^{\circ}C$ to $150^{\circ}C$ (unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Operating Point	B_{OP}	$T_A = -40^{\circ}C$	1.4	3.2	4.7	mT
		$T_A = 25^{\circ}C$	1.4	3.0	4.7	mT
		$T_A = 150^{\circ}C$	0.7	2.6	5.0	mT
		$V_{DD} = 2.7V$ to $24V$	0.5		5.8	mT
Release Point	B_{RP}	$T_A = -40^{\circ}C$	-4.7	-3.2	-1.4	mT
		$T_A = 25^{\circ}C$	-4.7	-3.0	-1.4	mT
		$T_A = 150^{\circ}C$	-5	-2.6	-0.5	mT
		$V_{DD} = 2.7V$ to $24V$	-5.8		1.5	mT
Temperature Coefficient ⁽¹⁾	TC			-1100		ppm/ $^{\circ}C$

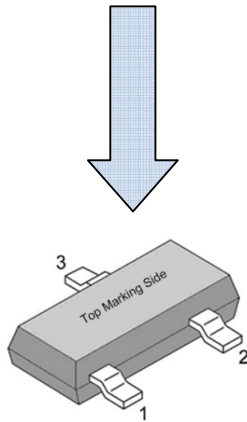
Table 2: Magnetic specifications

7 Output Behaviour versus Magnetic Pole

DC Operating Parameters $T_A = -40^{\circ}C$ to $150^{\circ}C$, $V_{DD} = 2.7V$ to $24V$ (unless otherwise specified)

Parameter	Test Conditions	OUT
South pole	$B > B_{OP}$	Low (V_{Dson})
North pole	$B < B_{RP}$	High (V_{PU}) ⁽²⁾

Table 3: Output behaviour versus magnetic pole ⁽³⁾



SE Pin No	Name	Type	Function
1	VDD	Supply	Supply Voltage pin
2	OUT	Output	Open Drain output pin
3	GND	Ground	Ground pin

¹ Temperature Coefficient is calculated using the following formula:

$$\frac{B_{T2} - B_{T1}}{B_{25^{\circ}C} \times (T_2 - T_1)} * 10^6, \text{ ppm / } ^{\circ}C; T_1 = -40^{\circ}C; T_2 = 150^{\circ}C, \text{ value guaranteed by design and verified by characterization, not production tested}$$

² Default Output state during power-up

³ Magnetic pole facing the branded/top side of the package

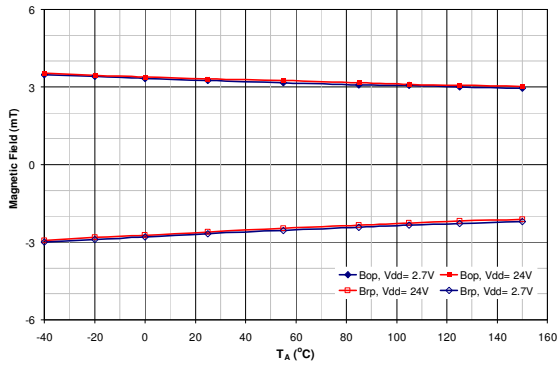


MLX92211LSE

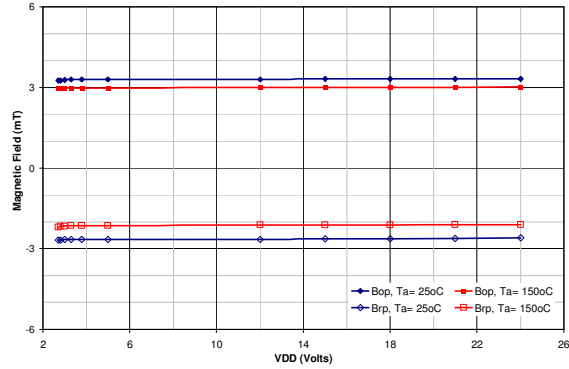
Hall Effect Latch – 2nd Generation
High Sensitivity

Performance Graphs

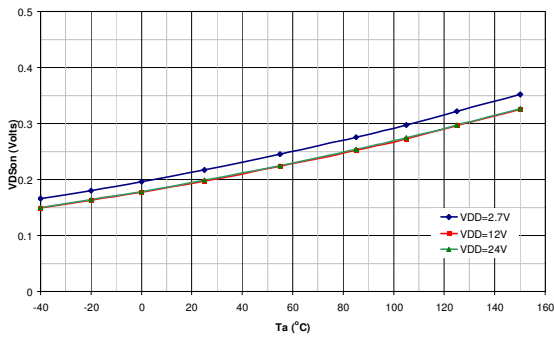
7.1 Magnetic parameters vs. T_A



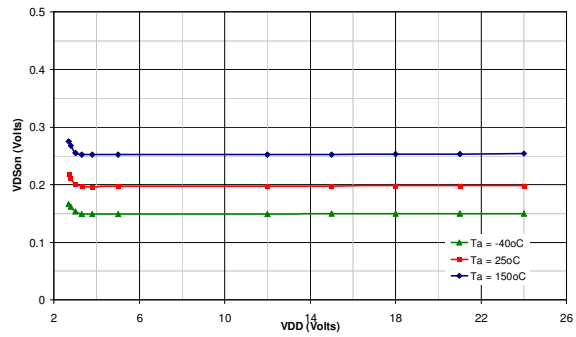
7.2 Magnetic parameters vs. V_{DD}



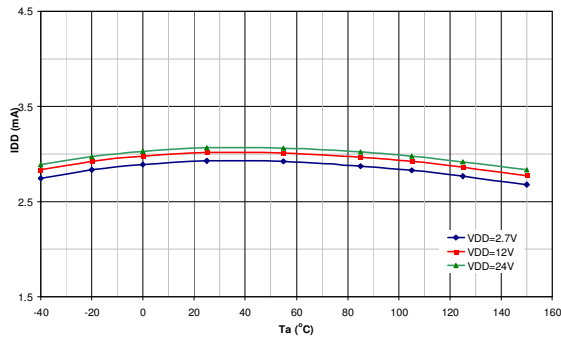
7.3 V_{Dson} vs. T_A



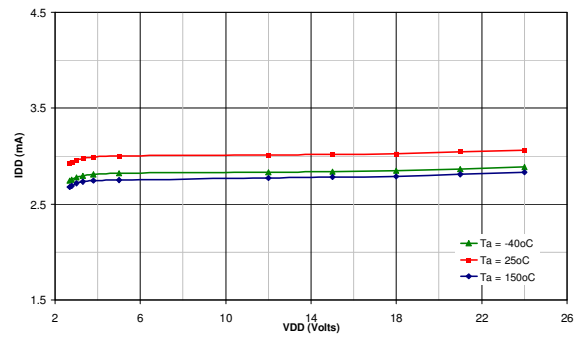
7.4 V_{Dson} vs. V_{DD}



7.5 I_{DD} vs. T_A



7.6 I_{DD} vs. V_{DD}



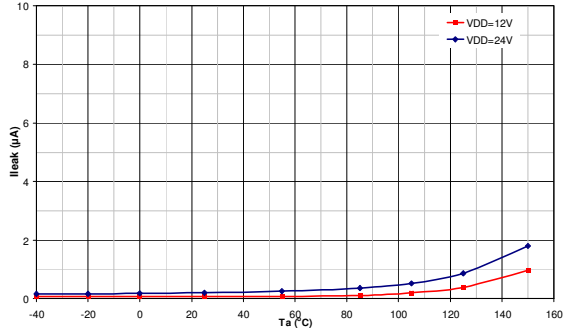


MLX92211LSE

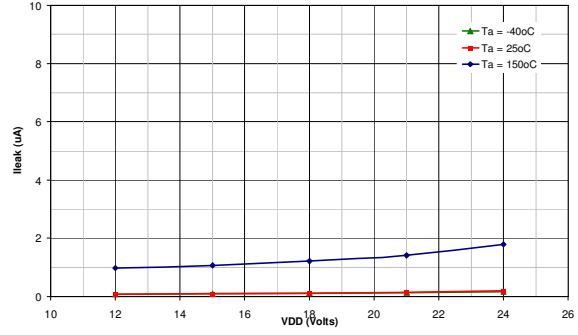
Hall Effect Latch – 2nd Generation

High Sensitivity

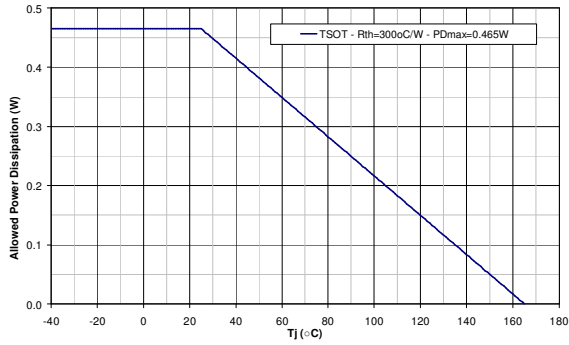
7.7 I_{LEAK} vs. T_A



7.8 I_{LEAK} vs. V_{DD}

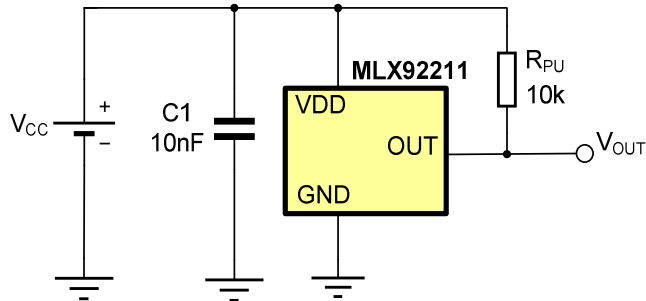


7.9 Power Derating vs. T_A



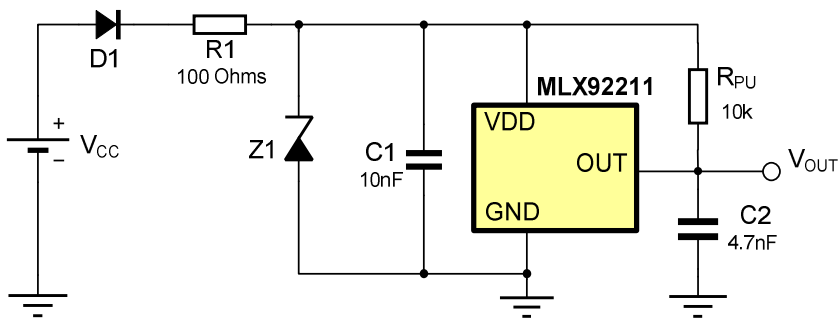
8 Application Information

8.1 Typical Three-Wire Application Circuit

**Notes:**

1. For proper operation, a 10nF to 100nF bypass capacitor should be placed as close as possible to the V_{DD} and ground pin.
2. The pull-up resistor R_{PU} value should be chosen in to limit the current through the output pin below the maximum allowed continuous current for the device.
3. A capacitor connected to the output is not needed, because the output slope is generated internally.

8.2 Automotive and Harsh, Noisy Environments Three-Wire Circuit

**Notes:**

1. For proper operation, a 10nF to 100nF bypass capacitor should be placed as close as possible to the V_{DD} and ground pin.
2. The device could tolerate negative voltage down to -27V, so if negative transients over supply line $V_{PEAK} < -32V$ are expected, usage of the diode D1 is recommended. Otherwise only R1 is sufficient.

When selecting the resistor R1, three points are important:

- the resistor has to limit I_{DD}/I_{DDREV} to 50mA maximum
- the resistor has to withstand the power dissipated in both over voltage conditions ($V_{R1}^2/R1$)
- the resulting device supply voltage V_{DD} has to be higher than V_{DD min} ($V_{DD} = V_{CC} - R1 \cdot I_{DD}$)

3. The device could tolerate positive supply voltage up to +27V (until the maximum power dissipation is not exceeded), so if positive transients over supply line with $V_{PEAK} > 32V$ are expected, usage a zener diode Z1 is recommended. The R1-Z1 network should be sized to limit the voltage over the device below the maximum allowed.



MLX92211LSE

*Hall Effect Latch – 2nd Generation
High Sensitivity*

9 Standard information regarding manufacturability of Melexis products with different soldering processes

Our products are classified and qualified regarding soldering technology, solderability and moisture sensitivity level according to following test methods:

Reflow Soldering SMD's (Surface Mount Devices)

- IPC/JEDEC J-STD-020
Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices (classification reflow profiles according to table 5-2)
- EIA/JEDEC JESD22-A113
Preconditioning of Nonhermetic Surface Mount Devices Prior to Reliability Testing (reflow profiles according to table 2)

Wave Soldering SMD's (Surface Mount Devices) and THD's (Through Hole Devices)

- EN60749-20
Resistance of plastic- encapsulated SMD's to combined effect of moisture and soldering heat
- EIA/JEDEC JESD22-B106 and EN60749-15
Resistance to soldering temperature for through-hole mounted devices

Iron Soldering THD's (Through Hole Devices)

- EN60749-15
Resistance to soldering temperature for through-hole mounted devices

Solderability SMD's (Surface Mount Devices) and THD's (Through Hole Devices)

- EIA/JEDEC JESD22-B102 and EN60749-21
Solderability

For all soldering technologies deviating from above mentioned standard conditions (regarding peak temperature, temperature gradient, temperature profile etc) additional classification and qualification tests have to be agreed upon with Melexis.

The application of Wave Soldering for SMD's is allowed only after consulting Melexis regarding assurance of adhesive strength between device and board.

Melexis is contributing to global environmental conservation by promoting **lead free** solutions. For more information on qualifications of **RoHS** compliant products (RoHS = European directive on the Restriction Of the use of certain Hazardous Substances) please visit the quality page on our website: <http://www.melexis.com/quality.aspx>

10 ESD Precautions

Electronic semiconductor products are sensitive to Electro Static Discharge (ESD). Always observe Electro Static Discharge control procedures whenever handling semiconductor products.

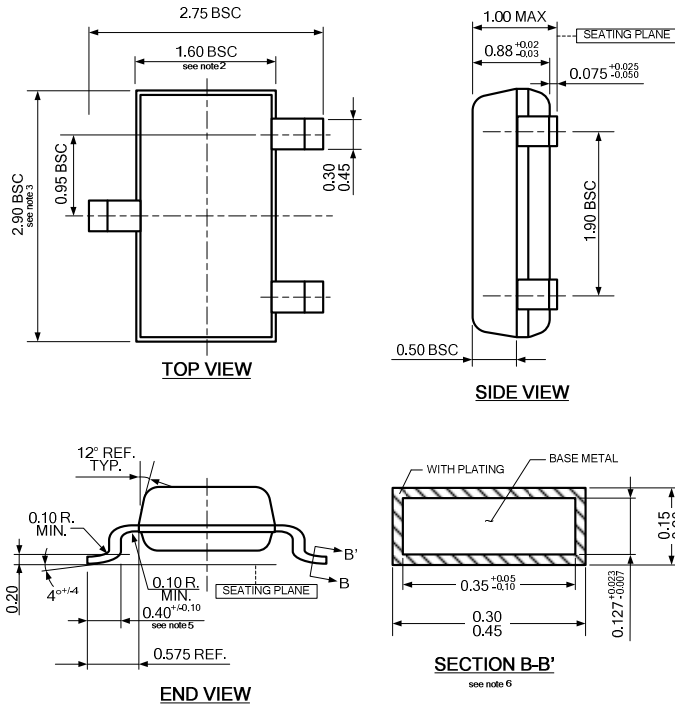


MLX92211LSE

Hall Effect Latch – 2nd Generation
High Sensitivity

11 SE Package (TSOT-23)

11.1 Package Outline Drawing & Hall Plate Position

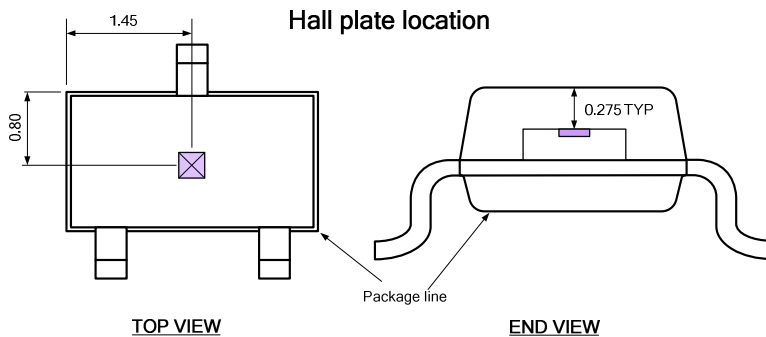


Notes:

1. All dimensions are in millimeters
2. Outermost plastic extreme width does not include mold flash or protrusions. Mold flash and protrusions shall not exceed 0.15mm per side.
3. Outermost plastic extreme length does not include mold flash or protrusions. Mold flash and protrusions shall not exceed 0.25mm per side.
4. The lead width dimension does not include dambar protrusion. Allowable dambar protrusion shall be 0.07mm total in excess of the lead width dimension at maximum material condition.
5. Dimension is the length of terminal for soldering to a substrate.
6. Dimension on SECTION B-B' applies to the flat section of the lead between 0.08mm and 0.15mm from the lead tip.
7. Formed lead shall be planar with respect to one another with 0.076mm at seating plane.

Marking:

Top side:
Bottom side:

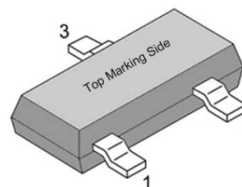


Notes:

1. All dimensions are in millimeters

SE Pin No	Name	Type	Function
1	VDD	Supply	Supply Voltage pin
2	OUT	Output	Open Drain output pin
3	GND	Ground	Ground pin

Table 4: SE Package pinout





MLX92211LSE

Hall Effect Latch – 2nd Generation
High Sensitivity

12 Disclaimer

Devices sold by Melexis are covered by the warranty and patent indemnification provisions appearing in its Term of Sale. Melexis makes no warranty, express, statutory, implied, or by description regarding the information set forth herein or regarding the freedom of the described devices from patent infringement. Melexis reserves the right to change specifications and prices at any time and without notice. Therefore, prior to designing this product into a system, it is necessary to check with Melexis for current information. This product is intended for use in normal commercial applications. Applications requiring extended temperature range, unusual environmental requirements, or high reliability applications, such as military, medical life-support or life-sustaining equipment are specifically not recommended without additional processing by Melexis for each application.

The information furnished by Melexis is believed to be correct and accurate. However, Melexis shall not be liable to recipient or any third party for any damages, including but not limited to personal injury, property damage, loss of profits, loss of use, interrupt of business or indirect, special incidental or consequential damages, of any kind, in connection with or arising out of the furnishing, performance or use of the technical data herein. No obligation or liability to recipient or any third party shall arise or flow out of Melexis' rendering of technical or other services.

© 2012 Melexis NV. All rights reserved.

For the latest version of this document, go to our website at
www.melexis.com

Or for additional information contact Melexis Direct:

Europe, Africa, Asia:

Phone: +32 1367 0495
E-mail: sales_europe@melexis.com

America:

Phone: +1 248 306 5400
E-mail: sales_usa@melexis.com

ISO/TS 16949 and ISO14001 Certified